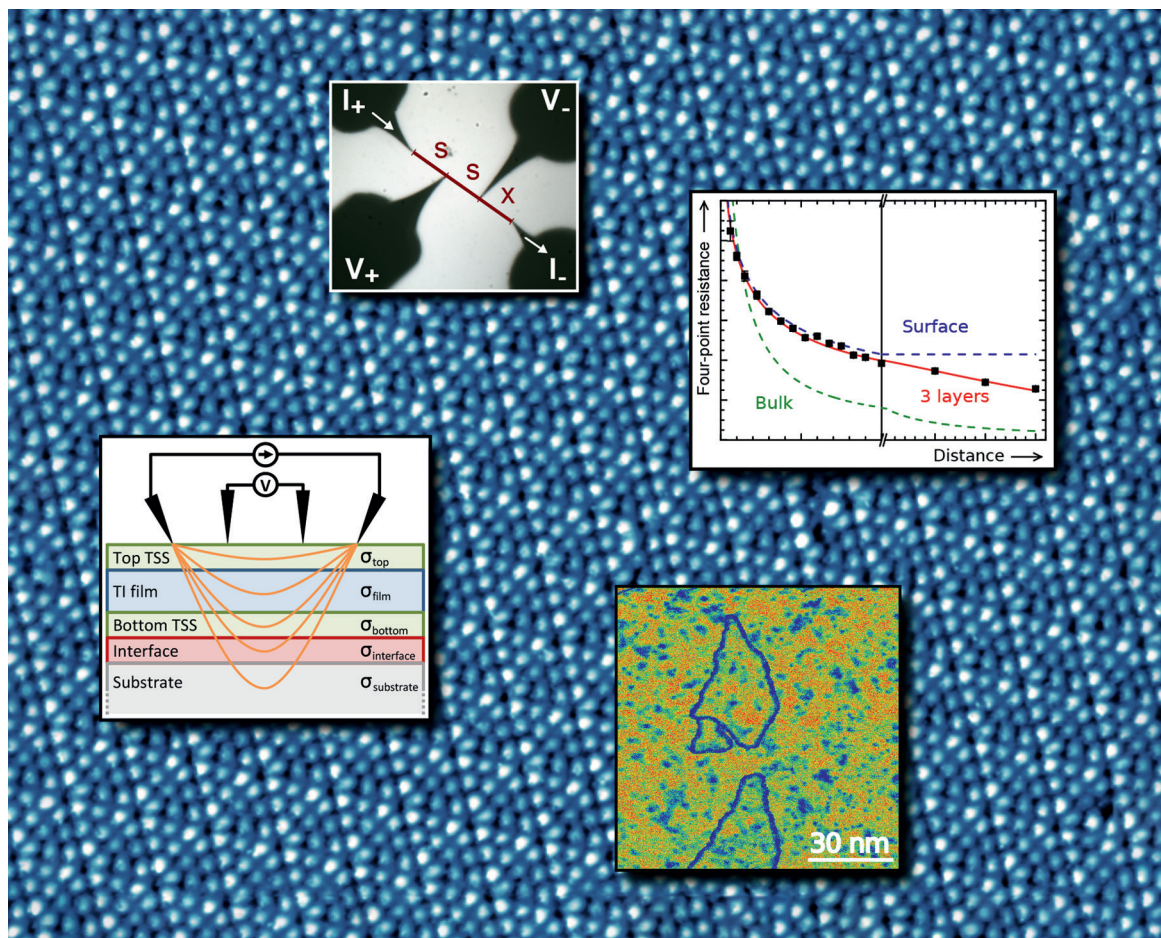




Disentangling parallel conduction channels by charge transport measurements on surfaces with a multi-tip scanning tunneling microscope

Sven Just

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Forschungszentrum Jülich GmbH
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